

Amendments to the Specification

Please replace the abstract with the following amended abstract:

A semiconductor device is provided with a FET having a sufficiently small short channel effect ~~as well as~~ and sufficiently small junction capacitance and junction ~~leakage~~ leakage current. The FET ~~comprises~~ includes a channel region formed in a silicon substrate, a gate electrode formed on the channel region through the intermediary of a gate insulting film, heavily doped regions, and pocket regions. The pocket regions are formed ~~so as~~ to extend from inside the heavily doped regions, respectively, over inside the channel region. Because a pocket sub-region inside the respective heavily doped regions is formed ~~so as~~ to be located in regions shallower than the respective lower end faces of the heavily doped regions, junction capacitance and junction ~~leakage~~ leakage current are reduced. Further, because respective pocket sub-regions inside the channel region are formed in regions deeper than the respective pocket sub-regions inside the heavily doped regions, a short channel effect can be reduced.